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Data 011001 1101 D1 12 00002 171

POWER OVER ETHERNET (PoE) EQUIPMENT PROTECTION

6.0 KP BIPOLAR TRANSIENT VOLTAGE SUPPRESSOR DIODE CELLS

FEATURES

- Lowest Electrical & Thermal Resistance Ideally Suited For Preventing Overvoltage/Overcurrent Damage to Power over Ethernet (PoE) Equipment
- VOID FREE VACUUM DIE SOLDERING For Lowest Electrical/Thermal Resistance And Maximum Mechanical Strength & Heat Dissipation (Solder Voids: Typical ≤ 2%, Max. ≤ 10% of Die Area)
- Round Die For High Power Heavy Duty Performance
- High Heat Handling Capability With Very Low Thermal Stress
- Proprietary Junction Passivation For Superior Reliability And Performance

RoHS COMPLIANT

MECHANICAL DATA

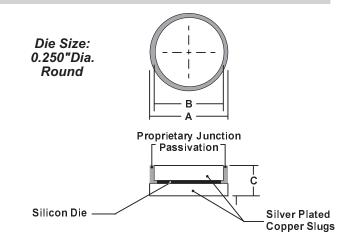
 Finish: All external surfaces are silver plated for corrosion resistance superior solderability

• Soldering Temperature: 282 °C maximum

Mounting Position: Any

• Polarity: Bipolar

MECHANICAL SPECIFICATION



D.114	INCHES		
DIM	NOM	+/-	
Α	0.285	0.003	
В	0.258	0.003	
С	0.098	0.004	

MAXIMUM RATINGS & ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified.

PARAMETER		RATINGS	UNITS
Series Number		BP6.0-23	
Breakdown Voltage (Cells Begin to Conduct) (See Note 1)	VBR	23.30 +/- 5%	VOLTS
Test Current (To Determine VBR)	lτ	5	mA
Clamping Voltage During a 10/1000μS Transient	VC(10)	32.4 Max	VOLTS
Maximum Current Conducted During a 10/1000μSTransient	IPPM(10)	154 Min	AMPS
Reverse Stand Off Voltage (Voltage at Which IR Measured)	Vwm	20	VOLTS
Maximum Current Conducted at Vwm	lR	1.25 Max	μ Α
Maximum Current Conducted During 8/20 μS Transient		1500 M in	AMPS
Clamping Voltage During 8/20 μS Transient		38 Max	VOLTS

Notes: (1) Diode cell breakdown voltage can be tailored to meet your specific application requirements. Please Contact Us for details.